



PATENT  
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Ulrike Gruening et al.

Serial No.: 09/669,585

Filing Date: September 26, 2000

Entitled: IMPROVED TRENCH CAPACITOR  
MEMORY CELL

Docket No.: 00P7925US (IFX-060PUS)

Group Art Unit: 2811

Examiner: C. Nguyen

#9/B  
3/12/03  
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By: Tanya Blount  
Tanya Blount

RESPONSE

BOX RCE  
Commissioner for Patents  
Washington, D.C. 20231

In response to the Final Office Action date mailed December 23, 2002, please amend the above-identified application as follows:

In the Claims:

A clean copy of the amended claims is below, a comparison copy is attached:

- B<sup>1</sup>
1. (Twice Amended) A memory cell comprising:  
a trench capacitor formed in a substrate;  
a shallow transistor trench (STT) formed in the substrate;  
a transistor comprising:  
a first diffusion region, the first diffusion region couples the capacitor to  
a gate of the transistor;